L Number	Hits	Search Text	DB	Time stamp
1	20747	((crystal or crystalline or crystallographic)	USPAT;	2004/09/17
•		adj orientation)	US-PGPUB;	20:29
			EPO; JPO;	
			DERWENT;	,
	•	·	IBM_TDB	
2	89	(first adj (crystal or crystalline or	USPAT;	2004/09/17
		crystallographic) adj orientation)	US-PGPUB;	20:29
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	36	layer near10 (first adj (crystal or crystalline	USPAT;	2004/09/17
		or crystallographic) adj orientation)	US PGPUB;	20:30
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
4	27	(layer near10 (first adj (crystal or	USPAT;	2004/09/17
		crystalline or crystallographic) adj	US-PGPUB;	20:31
		orientation))same (layer near10 (second adj	EPO; JPO;	
	<i>?</i>	(crystal or crystalline or crystallographic)	DERWENT;	
		adj orientation))	!BM_TDB	
5	27	(layer near10 (first adj (crystal or	USPAT;	2004/09/17
		crystalline or crystallographic) adj	US-PGPUB;	20:39
		orientation)) same (layer near10 (second	EPO; JPO;	
		adj (crystal or crystalline or	DERWENT;	
		crystallographic) adj orientation))	IBM_TDB	
6	0	(layer near10 (first adj (crystal or	USPAT;	2004/09/17
		crystalline or crystallographic) adj	US-PGPUB;	20:34
		orientation)) same (layer near10 (second	EPO; JPO;	
		adj (crystal or crystalline or	DERWENT;	
		crystallographic) adj orientation)) and	IBM_TDB	
_		(hybrid adj substrate)		
7	0	((first adj (crystal or crystalline or	USPAT;	2004/09/17
		crystallographic) adj orientation)) same	US-PGPUB;	20:35
		((second adj (crystal or crystalline or	EPO; JPO;	
		crystallographic) adj orientation)) and	DERWENT;	
		(hybrid adj substrate)	IBM_TDB	
8	798	hybrid adj substrate	USPAT;	2004/09/17
,			US-PGPUB;	20:36
		· ·	EPO; JPO;	
			DERWENT;	
	20	(bybrid adi aubatuata) and (farant-l an	IBM_TDB	2004/00/47
9	26	(hybrid adj substrate) and ((crystal or	USPAT;	2004/09/17
		crystalline or crystallographic) adj	US-PGPUB;	20:37
İ		orientation)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

12	0	((semiconductor adj layer) near3 (first adj	USPAT;	2004/09/17
		(crystal or crystalline or crystallographic)	US-PGPUB;	20:40
		adj orientation)) same ((semiconductor adj	EPO; JPO;	
		layer) near10 (second adj (crystal or	DERWENT;	
		crystalline or crystallographic) adj	IBM_TDB	
		orientation))		
11	3	((semiconductor adj layer) near3 (first adj	USPAT;	2004/09/17
		(crystal or crystalline or crystallographic)	US-PGPUB;	20:44
		adj orientation)) same (layer near10	EPO; JPO;	
		(second adj (crystal or crystalline or	DERWENT;	
		crystallographic) adj orientation))	IBM_TDB	
10	3	(semiconductor adj layer near3 (first adj	USPAT;	2004/09/17
		(crystal or crystalline or crystallographic)	US-PGPUB;	20:40
		adj orientation)) same (layer near10	EPO; JPO;	
,		(second adj (crystal or crystalline or	DERWENT:	
		crystallographic) adj orientation))	IBM_TDB	
13	0	((semiconductor adj layer) near5 (first adj	USPAT;	2004/09/17
		(crystal or crystalline or crystallographic)	US-PGPUB;	20:44
		adj orientation)) same ((semiconductor adj	EPO; JPO;	
		layer) near5 (second adj (crystal or	DERWENT;	
		crystalline or crystallographic) adj	IBM_TDB	
		orientation))		
14	o	((semiconductor adj layer) near10 (first adj	USPAT;	2004/09/17
		(crystal or crystalline or crystallographic)	US-PGPUB;	20:45
		adj orientation)) same ((semiconductor adj	EPO; JPO;	
•		layer) near10 (second adj (crystal or	DERWENT;	
		crystalline or crystallographic) adj	IBM_TDB	
		orientation))	15155	
15	1	((semiconductor adj layer) near10 (first adj	USPAT;	2004/09/17
••	•	(crystal or crystalline or crystallographic)	US-PGPUB;	20:45
		adj orientation)) and ((semiconductor adj	EPO; JPO;	20.40
		layer) near10 (second adj (crystal or	DERWENT;	
		crystalline or crystallographic) adj	IBM_TDB	
		orientation))	15111_155	
16	5	(ieong or reznicek or yang) and (hybrid adj	USPAT;	2004/09/17
		substrate)	US-PGPUB;	20:46
		Janotiato	EPO; JPO;	20.40
			DERWENT;	
			IBM_TDB	
17	30	(ieong or reznicek or yang) and ((crystal or	USPAT;	2004/09/17
• •	. 30	crystalline or crystallographic) adj	US-PGPUB;	20:47
	,	orientation).clm.	1	2014 <i>1</i>
		orientation).cim.	EPO; JPO;	
			DERWENT;	
40		(icons or remisely or result and days	IBM_TDB	2004/00/47
18	8	(ieong or reznicek or yang) and (layer	USPAT;	2004/09/17
		near10 ((crystal or crystalline or	US-PGPUB;	20:48
		crystallographic) adj orientation)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

19	1	(ieong or reznicek or yang) and (layer	USPAT;	2004/09/17
		near10 ((first or second) adj (crystal or	US-PGPUB;	20:48
		crystalline or crystallographic) adj	EPO; JPO;	
		orientation)).clm.	DERWENT;	
			IBM_TDB	
20	18	(layer near10 ((first or second) adj (crystal	USPAT;	2004/09/17
		or crystalline or crystallographic) adj	US-PGPUB;	20:48
		orientation)).clm.	EPO; JPO;	
			DERWENT;	
]		IBM_TDB	
21	18	(layer near5 ((first or second) adj (crystal or	USPAT;	2004/09/17
		crystalline or crystallographic) adj	US-PGPUB;	20:49
		orientation)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
22	1	(semiconductor near5 layer near5 ((first or	USPAT;	2004/09/17
		second) adj (crystal or crystalline or	US-PGPUB;	20:50
		crystallographic) adj orientation)).clm.	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
23	5	(semiconductor near5 layer near5 ((first or	USPAT;	2004/09/17
		second) adj (crystal or crystalline or	US-PGPUB;	20:50
		crystallographic) adj orientation))	EPO; JPO;	
]		DERWENT;	
			IBM TDB	